

In the Claims:

1. (Currently Amended) A carrier ~~for receiving and electrically contacting individually separated dies for the testing and/or burn-in of the same~~, wherein the carrier comprises:

a support structure;

first contacts disposed on the support structure and arranged in a ~~grid~~ pattern ~~corresponding to a die to be contacted~~;

elastomer bumps provided on the ~~first contacts~~ support structure;

second contacts formed on the elastomer bumps, wherein the second contacts are electrically connected to the first contacts, wherein the electrical connection of the first contacts to the second contacts is established by conductor tracks rising on the elastomer bumps in a spiral or arcuate manner to a tip of the elastomer bumps; and

at least one opening in the support structure wherein ~~dies~~ a die placed on the support structure can be drawn against the elastomer bumps by a force generated by a vacuum and applied through the opening.

2. (Original) The carrier of claim 1 wherein the second contacts are comprised of gold.

3. (Canceled)

4. (Currently Amended) The carrier of claim ~~[[3]]~~ 1 wherein the conductor tracks comprise a copper-nickel-gold layer construction.

5. (Currently Amended) The carrier of claim [[1]] 5 wherein a gold-gold contact is realized between the die and the carrier by a re-distribution layer arranged on the die.

6. (Original) The carrier of claim 1 wherein the re-distribution layer comprises a copper-nickel-gold layer construction.

7. (Original) The carrier of claim 1 and further comprising a cover overlying the support structure.

8. (Original) The carrier of claim 7 wherein the cover is formed as a spring element.

9. (Currently Amended) A method of processing a semiconductor die, the method comprising:

providing a semiconductor die, the die including contacts formed in a pattern;

providing a carrier, the carrier comprising first contacts disposed over a surface of a support structure, elastomer bumps provided on the first contacts, and second contacts formed on the elastomer bumps, wherein the second contacts are arranged in a pattern corresponding to the pattern on the die, the second contacts being electrically coupled to the first contacts, wherein the electrical connection of the first contacts to the second contacts is established by conductor tracks rising on the elastomer bumps in a spiral or arcuate manner to a tip of the elastomer bumps;

placing the die on the support structure of the carrier;

securing the contacts of the die against the elastomer bumps by a predetermined force

generated by a vacuum; and

evaluating the semiconductor die.

10. (Currently Amended) The method of claim 9 wherein the die is ~~fixed~~ secured by a vacuum until the contacts of the die are ~~secured~~ fixed against the elastomer bumps.

11. (Original) The method of claim 10 wherein the fixing of the die takes place by a cover, wherein the cover compresses the elastomer bumps with a predetermined pressing force after placing.

12. (Original) The method of claim 11 wherein the pressing force is approximately 2 to 8 grams per elastomer bump.

13. (Original) The method of claim 11 wherein the cover is formed as a spring element.

14. (Original) The method of claim 9 wherein providing a semiconductor die comprises:
fabricating a wafer that includes a plurality of semiconductor dies; and
separating the wafer to provide the semiconductor die.

15. (Original) The method of claim 9 wherein evaluating the semiconductor die comprises testing the semiconductor die.

16. (Original) The method of claim 9 wherein evaluating the semiconductor die comprises burning-in the semiconductor die.
17. (Original) The method of claim 9 wherein the second contacts of the carrier are comprised of gold.
18. (Canceled)
19. (Currently Amended) The carrier of claim ~~[[18]]~~ 9 wherein the conductor tracks comprise a copper-nickel-gold layer construction.
20. (Original) The carrier of claim 9 wherein a gold-gold contact is realized between the die and the carrier by re-distribution layers being arranged on the die, and wherein the re-distribution layers comprise a copper-nickel-gold layer construction.
21. (New) A carrier comprising:
- a support structure;
 - a frame fastened on the support structure and including four walls to surround a surface of the support structure of a size that corresponds to a size of a semiconductor die, an upper portion of the walls being beveled in a direction toward the surface;
 - first contacts disposed on the surface of the support structure;
 - elastomer bumps disposed on the surface of the support structure;

second contacts formed on the elastomer bumps, wherein the second contacts are electrically connected to the first contacts; and

at least one opening in the support structure wherein a die placed on the support structure can be drawn against the elastomer bumps by a force generated by a vacuum and applied through the opening.

22. (New) The carrier of claim 21 and further comprising a cover overlying the support structure, wherein the cover is formed as a spring element.